## Supplementary Information

## Morphology Fixing Agent for PC<sub>60</sub>BM in Planar-Type Perovskite Solar Cells for Enhanced Stability

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Figure S1. SEM cross sectional image of the PEDOT:PSS and the MAPbI $_3$  layer.







Figure S3. J-V characterization of the PSCs depending on the different thicknesses of MAPbI<sub>3</sub>. The  $PC_{60}BM$  layer was initially coated to a thickness of ~ 70 nm for thickness optimizing of MAPbI<sub>3</sub>.



Figure S4. J-V curves of the PSCs with different thicknesses of  $TiO_x$  layer (0 to 20 nm).



Figure S5. J-V curves of the PSCs measured by forward and reverse scans, fabricated by (a) without and (b) with the  $TiO_x$  layer.



Figure S6. Photographs of the devices without and with the  $TiO_x$  morphological fixing agent and after the stability test: (a, b) PSCs without  $TiO_x$ , and (c, d) PSCs with  $TiO_x$ ; (a, c) as cast and (b, d) after 3 days.



Figure S7. SEM surface images of (a, b) MAPbI<sub>3</sub>, (c, d) MAPbI<sub>3</sub>/PC<sub>60</sub>BM, (e, f) MAPbI<sub>3</sub>/PC<sub>60</sub>BM/TiO<sub>x</sub>; (b, d, f) are the SEM images after 3 days.

PC <sub>60</sub> BM (70nm)	$V_{OC}(V)$	J <sub>SC</sub> (mA/cm <sup>2</sup> )	FF (%)	PCE (%)
MAPbI <sub>3</sub> (190nm)	0.844	13.18	70.2	7.81
MAPbI <sub>3</sub> (250nm)	0.793	11.10	58.4	5.14
MAPbI <sub>3</sub> (290nm)	0.854	12.53	46.2	4.95

Table S1. Electrical parameters of the PSCs depending on the controlled thickness of MAPbI<sub>3</sub> as shown in Fig. S3.

PC <sub>60</sub> BM (100nm)	$V_{OC}(V)$	J <sub>SC</sub> (mA/cm <sup>2</sup> )	FF (%)	Eff. (%)
without TiOx	0.875	12.58	72.8	8.01
With TiOx (~5nm)	0.917	13.01	72.8	8.68
With TiOx (~10nm)	0.928	14.78	75.9	10.41
With TiOx (~20nm)	0.913	13.41	74.9	9.17

Table S2. Electrical parameters of the PSCs depending on different thickness of  $TiO_x$  layer as corresponded with Fig. S4.

PSCs	Scan direction	V <sub>OC</sub> (V)	J <sub>SC</sub> (mA/cm <sup>2</sup> )	FF (%)	PCE (%)
Without	Forward	0.872	13.27	67.5	7.81
	Reverse	0.875	13.53	70.7	8.37
With $TiO_x$	Forward	0.928	14.78	75.9	10.41
	Reverse	0.928	14.89	76.7	10.59

Table S3. Electrical parameters of the PSCs without and with the  $TiO_x$  layer depending on the different scan directions as shown in Fig. S5.